

5 **In the Claims:**

Applicants hereby submit amended claims, including a complete listing of all claims in the application with the status of each claim in parentheses.

1.- 2. (canceled)

10 3. (canceled)

4. (canceled)

5. (canceled)

6. (canceled)

7. (previously presented) A method for formation of an ion beam that provides  
15 carbon deposition over a substrate, the ion beam produced by inductively ionizing an acetylene plasma within a plasma volume and capacitatively coupling the plasma so as to form a stream of ions from within the plasma volume, the method comprising:

moving a magnetic field through the plasma volume to promote even resonant inductive ionization and homogenize the ion beam which deposits carbon over the substrate, wherein the  
20 magnetic field rotates with a frequency of less than 10,000 Hz.

8. (previously presented) A method as claimed in claim 7, wherein moving the magnetic field comprises selectively energizing magnetic coils disposed about the plasma volume.

9. (previously presented) A method as claimed in claim 7, wherein the magnetic  
25 field rotates through the plasma volume with a frequency which is much less than the frequency of an alternating induction potential within the plasma volume.

- 5            10.    (previously presented) A method as claimed in claim 7, wherein the magnetic field is transverse and rotates about an axis which is substantially normal to a capacitatively coupled extraction grid within the plasma volume.
11.    (previously presented) A method as claimed in claim 7, wherein the magnetic field rotates with a frequency of less than 100 Hz.
- 10           12.-15. (canceled).
16.    (canceled)
17.    (canceled)
18.    (previously presented) A method as in claim 7, wherein the carbon is deposited on the substrate at a rate in a range from 20 Å per second to 100 Å per second.
- 15           19.    (canceled)
20.    (canceled)
21.    (previously presented) A method as in claim 7, wherein the substrate includes a magnetic recording medium.
22.    (previously presented) A method as in claim 7, wherein the substrate includes a
- 20    semiconductor material.
23.    (canceled)
24.    (canceled)
25.    (canceled)
26.    (canceled)
- 25           27.    (canceled)
28.    (canceled)
29.    (canceled)

- |    |     |            |
|----|-----|------------|
| 5  | 30. | (canceled) |
|    | 31. | (canceled) |
|    | 32. | (canceled) |
|    | 33. | (canceled) |
|    | 34. | (canceled) |
| 10 | 35. | (canceled) |
|    | 36. | (canceled) |
|    | 37. | (canceled) |
|    | 38. | (canceled) |
|    | 39. | (canceled) |
| 15 | 40. | (canceled) |